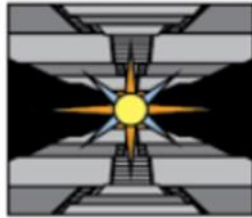


HPSP-16 Conference



High Pressure in Semiconductor Physics

Mexico City
6 - 8 August 2014

<http://hpsp16.cinvestav.mx>

SCHEDULE

HPSP-16 High Pressure in Semiconductor Physics Mexico City August 6 – 8, 2014					
Hour	Tuesday 5	Wednesday 6	Thursday 7	Friday 8	
08:00 - 09:00		Registration	Registration		
09:00 - 09:20		Opening Session	M. Brotons-Gisbert	B. Haberl	
09:20 - 09:40			A. Polian	J. E. Bradby	
09:40 - 10:10		N. E. Christensen	M. Grinberg	Y. Fujiwara	
10:10 - 10:30		B. A. Weinstein	K. Syassen	M. Pravica	
10:30 - 10:50		A. Kaminska	R. Boehler	K. Takarabe	
10:50 - 11:20		Coffee Break	Coffee Break	Closing Session	
11:20 - 11:50		A. Romero	B. Liu		
11:50 - 12:10		D. Olguín	Memorial Session	Conference Excursion to Teotihuacan Pyramids	
12:10 - 12:40		Y. Le Godec			
12:40 - 15:00		Lunch Break	Lunch Break		
15:00 - 15:30		A. Goñi	POSTER SESSION		
15:30 - 15:50		H. Elsayed			
15:50 - 16:10		S. V. Ovsyannikov			
16:10 - 16:40		A. Akrap			
16:40 - 17:00					
17:00 – 17:30					Arrival to the hotel
17:30 - 18:00	REGISTRATION	Welcome Reception			
18:00 - 18:30					
18:30 – 19:00					
19:00 - 19:30					
19:30 – 20:00					
20:00 – 21:00			Conference Dinner		
21:00 – 22:00					
22:00 – 23:00					

Oral sessions will take place in *Salón Juárez*

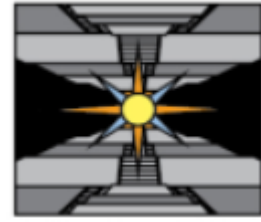
Welcome reception and poster session in *Bar Reforma*

Conference dinner in the lobby of the library of the Physics Department at Cinvestav

Lunch in *Restaurant Miró*

HPSP-16 Conference

High Pressure in Semiconductor Physics



The Sixteenth International Conference on High Pressure in Semiconductor Physics (HPSP-16) is organized by Cinvestav (Center for Research and Advanced Studies) in Mexico City, in the middle of one of the most attractive touristic zones. HPSP-16 is a satellite of the International Conference on the Physics of Semiconductors ([ICPS 2014](#)) to be held in Austin (USA) during the following week. HPSP is a biennial meeting with a long-standing tradition. The first two meetings took place in Poland (1985) and Montpellier (1986), recent HPSP conferences were held in Fortalez, Brazil (2008); Changchun, China (2010) and Montpellier, France (2012).

The aim of HPSP-16 is to allow young and experienced researchers from different fields to meet together during a single-session conference to present and discuss their latest theoretical and experimental results in the field of application of high pressure and other forms of high stress in the study of semiconductors. During the meeting a wide range of topics will be reviewed including advanced semiconductor materials, vibrational properties and electronic structures, phase transitions and of course the new devices and new techniques from physics under pressure.

Venue: Mexico City

In Spanish *Ciudad de México*, known also as DF is the capital of Mexico and one of the largest metropolitan areas in the world. It is the largest and most important political, cultural and educational city of the country and one of the most important financial centers in North America. It is located in the Valley of Mexico at an altitude of 2,240 m. The city was originally built on an island of Lake Texcoco by the Aztecs in 1325, it was known as Tenochtitlan. In 1524, the municipality of Mexico City was established, known as México Tenochtitlán. Later, in 1585 it was officially named Ciudad de México (Mexico City). Mexico City has a very comfortable weather and it is plenty of touristic attractions.

CONFERENCE COMMITTEES

Conference Chair: Isaac **HERNÁNDEZ-CALDERÓN**, Cinvestav, Mexico.

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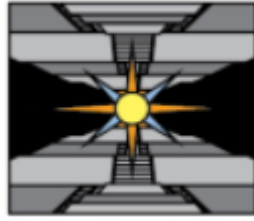
Miguel U. **Salazar Tovar**

Jose A. **Lorenzo Andrade**

Didier A. **Patiño Rodríguez**

Secretary: Mariana **del Castillo Sánchez**

HPSP-16 2014 Mexico City



Invited Speakers

Ana **Akrap**, *University of Geneva, Switzerland:*

"Electronic structure of topological insulators under high pressure by means of FTIR spectroscopy in DAC"

Niels **Christensen**, *Aarhus University, Denmark:*

"Indium-Gallium Nitride Alloys and Superlattices: Composition and Pressure Dependences"

Yasufumi **Fujiwara**, *Osaka University, Japan:*

"Strain dependent energy transfer from the GaN host to Eu ions in Eu-doped GaN grown on different substrates by organometallic vapor phase epitaxy"

Alejandro **Goñi**, *Institut de Ciència de Materials de Barcelona, Spain:*

"Using high pressure to unravel the nature of optical transitions in (In,Ga)As/GaP quantum dots"

Marek **Grinberg**, *University of Gdansk, Poland:*

"High pressure study of the Ln^{3+} and Ln^{2+} ions in solids"

Yann **Le Godec**, *Institut de minéralogie, de physique des matériaux et de cosmochimie, France:*

"High pressure synthesis of new superhard boron compounds"

Bingbing **Liu**, *Jilin University, China:*

"Fullerene under high pressure"

Aldo **Romero**, *West Virginia University, USA /Cinvestav, Mexico:*

"Large magnetic canting in perovskite fluorides under pressure from first principles: physics and beyond"

HPSP-16 Mexico City 6 – 8 August 2014

Special session devoted to the memory of
Prof. Manuel Cardona
Max-Planck Institute für Festkörperforschung, Stuttgart



Professor Manuel Cardona (7 September 1934 – 2 July 2014), was born in Barcelona, Spain. He is recognized as one of the most internationally renowned physicists.

He studied Physics at the University of Barcelona from 1950 to 1955. In 1956, he moved to Harvard University under the guidance of Prof. William Paul where he developed doctoral research on the quadratic photomagneto-electric effect in germanium and silicon; he obtained his doctorate in science from the University of Madrid in 1958. He also obtained a Ph. D. in Applied Physics from Harvard University in 1959 based on his work on the dielectric properties of germanium and silicon and their dependence on pressure and temperature. In 1959, he joined the staff of the RCA laboratories in Zurich, Switzerland; in 1961, he moved to the same company's laboratories in Princeton, USA. In 1964 became lecturer in Physics at Brown University in Providence. In 1971 moved to Stuttgart as a founding director of the then recently created Max Planck Institute for Solid State Research. He became emeritus of the Max Planck Society in 2000.



He was member of the editorial boards of highly reputed scientific publications, and member of innumerable scientific committees. He was a very prolific author and one of the most cited physicist of recent decades. His papers and books have a strong influence in the solid state physics community. He received many prestigious awards and honorary doctorates.



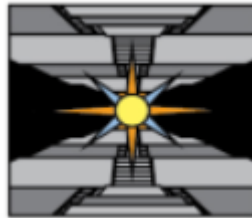
Inge and Manuel Cardona during a stay at Cinvestav in Mexico City. In August 2010 he received the Doctor honoris causa degree.

Manuel had a remarkable permanent and friendly open attitude to talk with students and young scientists. He guided several generations of prominent graduate students and postdocs. He had also a profound knowledge or literature, art and history and had strong political convictions.

Manuel and his wife Inge formed a delightful couple, always warmth and friendly, happy to help anyone in many different ways.

He was an enthusiastic and distinguished contributor of the HPSP conference. We honor his memory with deep gratitude.

HPSP-16 2014 Mexico City



SESSION CHAIRS

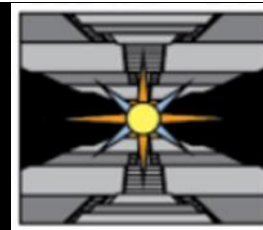
Chair	Day	Hour
Karl Syassen , <i>MPI for Solid State Research (Germany)</i>	Wednesday	09:40-10:50
Michael Pravica , <i>University of Nevada, Las Vegas (USA)</i>	Wednesday	11:20-12:40
Agata Kaminska , <i>Polish Academy of Sciences (Poland)</i>	Wednesday	15:00-16:40
Bernard Weinstein , <i>University of Buffalo (USA)</i>	Thursday	09:00-10:50
Kenichi Takarabe , <i>Okayama University of Science (Japan)</i>	Thursday	11:20-11:50
Peter Yu , <i>University of California (USA)</i>	Thursday	11:50-12:40
Andrés Cantarero , <i>University of Valencia (Spain)</i>	Friday	09:00-10:50

SPONSORS



HPSP-16 Conference

High Pressure in Semiconductor Physics



Mexico City, 6 – 8 August 2014

TUESDAY 5

Tuesday 17:00-19:30	REGISTRATION Hotel Lobby
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WEDNESDAY 6

Wednesday 09:00-09:40	OPENING SESSION Salón Juárez	
Inv-1 Wednesday 09:40-10:10 Page 1	N. E. Christensen Department of Physics and Astronomy, Aarhus University, Denmark	Indium-Gallium nitride alloys and superlattices: Composition and pressure dependences <i>N. E. Christensen, I. Gorczyca, A. Svane, T. Suski, K. Skrobas</i>
O-01 Wednesday 10:10-10:30 Page 2	B. A. Weinstein SUNY at Buffalo, Department of Physics, USA	Plastic deformation and high-pressure transitions in semiconductors <i>B. A. Weinstein, G. P. Lindberg</i>
O-02 Wednesday 10:30-10:50 Page 3	A. Kaminska Institute of Physics, Polish Academy of Sciences, Poland	Pressure-induced piezoelectric effects in ZnO/ZnMgO quantum wells <i>A. Kaminska, H. Teisseyre, S. Birner, A. Suchocki</i>
Wednesday 10:50-11:20	COFFEE BREAK	
Inv-2 Wednesday 11:20-11:50 Page 4	A. H. Romero West Virginia University, Cinvestav, Unidad Querétaro, USA	Large magnetic canting in perovskites under pressure from first-principles: Physics and beyond <i>A. H. Romero, A. C. Garcia-Castro, E. Bousquet</i>
O-03 Wednesday 11:50-12:10 Page 5	D. Olguín Departamento de Física, Centro de Investigación y de Estudios Avanzados del Instituto Politécnico Nacional, Mexico	Ab initio study of the low pressure phases of Ti₃O₅ <i>D. Olguín, E. Vallejo, A. Rubio-Ponce</i>
Inv-3 Wednesday 12:10-12:40 Page 6	Y. Le Godec IMPMC, UPMC Sorbonne Universités, CNRS, France	High pressure synthesis of new superhard boron compounds <i>Y. Le Godec, O. O. Kurakevych, V. L. Solozhenko</i>
Wednesday 12:40-15:00	LUNCH BREAK Restaurant Miró	

Inv-4 Wednesday 15:00-15:30 Page 7	A. R. Goñi ICREA and Institut de Ciencia de Materials de Barcelona - CSIC, Spain	Using high pressure to unravel the nature of optical transitions in (In,Ga)As/GaP quantum dots <i>A. R. Goñi, C. Robert, K. Pereira da Silva, M. O. Nestoklon, L. Pedesseau, C. Cornet, M. I. Alonso, P. Turban, J. M. Jancu, J. Even, O. Durand</i>
O-04 Wednesday 15:30-15:50 Page 8	H. Elsayed Instituto de Ciencia de Materiales, Universidad de Valencia, Spain	Ab initio study of different crystal phases of MgSe <i>H. Elsayed, A. Cantarero, D. Olguín, I. Hernández-Calderón</i>
O-05 Wednesday 15:50-16:10 Page 9	S. V. Ovsyannikov Bayerisches Geoinstitut, Universität Bayreuth, Germany	Semiconducting properties of metastable manganese oxides <i>S. V. Ovsyannikov, A. E. Karkin, N. V. Morozova, V. V. Shchennikov, E. Bykova, A. M. Abakumov, A. A. Tsirlin, K. V. Glazyrin, L. Dubrovinsky</i>
Inv-5 Wednesday 16:10-16:40 Page 10	A. Akrap DPMC, University of Geneva, Switzerland	Electronic structure of topological insulators under high pressure by means of FTIR spectroscopy in DAC <i>A. Akrap, M. Tran, A. Ubaldini, J. Teyssier, E. Giannini, Ph. Lerch, D. Van der Marel</i>
Wednesday 17:00-19:00	WELCOME RECEPTION Bar Reforma	
THURSDAY 7		
O-06 Thursday 09:00-09:20 Page 11	M. Brotons-Gisbert Institut de Ciència dels Materials Universitat de València, Spain	High pressure study of the optical properties of MoS₂ single crystal <i>M. Brotons-Gisbert, A. Segura, J. F. Sánchez-Royo</i>
O-07 Thursday 09:20-09:40 Page 12	A. Polian Sorbonne Universités, Institut de Minéralogie, de Physique des Matériaux, et de Cosmochimie and CNRS, France	High pressure properties of the chalcopyrite ZnGeP₂ <i>P. de Freitas Facanha Filho, A. Polian, L. Nataf, F. Baudelet, J. P. Itié, T. Irifune, M. Mikhailovich Philippov, A. Ivanovich Gribenyukov</i>
Inv-6 Thursday 09:40-10:10 Page 13	M. Grinberg Institute of Experimental Physics, University of Gdansk, Poland	High pressure study of Ln³⁺ and Ln²⁺ in solids <i>M. Grinberg</i>
O-08 Thursday 10:10-10:30 Page 14	K. Syassen Max-Planck-Institute for Solid State Physics, Germany	Transition metal compounds under pressure <i>K. Syassen</i>
O-09 Thursday 10:30-10:50 Page 15	R. Boehler Geophysical Laboratory, Carnegie Institution of Washington, USA	Surprise in the High-Pressure phase behavior of carbon <i>R. Boehler, L. Yang, A. Karandikar</i>
Thursday 10:50-11:20	COFFEE BREAK	

Inv-7 Thursday 11:20-11:50 Page 16	B. B. Liu State Key Lab of Superhard Materials, Jilin University, China	High pressure induced novel phase transition in nano structured fullerene crystals <i>B. B. Liu, M. G. Yao, L. Wang, D. D. Liu, W. Cui, B. Sundqvist</i>
Thursday 11:50-12:40	Memorial Session in honor of Manuel Cardona Peter Yu, Karl Syassen, Bernie Weinstein, Andrés Cantarero, Isaac Hernández-Calderón	
Thursday 12:40-15:00	LUNCH BREAK Restaurant Miró	
Thursday 15:00-17:30 Page 22	POSTER SESSION Bar Reforma	
Thursday 20:00-23:00	CONFERENCE DINNER Lobby of the Physics Department Library, Cinvestav. Bus departs at 7:30 pm.	
FRIDAY 8		
O-10 Friday 09:00-09:20 Page 17	B. Haberl Department of Electronic Materials Engineering, Research School of Physics and Engineering, Australian National University, Australia	New insights into the metalization of group IV elements <i>B. Haberl, M. Guthrie, B. D. Malone, J. S. Smith, S. V. Sinogeikin, G. Shen, M. L. Cohen, J. S. Williams, J. E. Bradby</i>
O-11 Friday 09:20-09:40 Page 18	J. E. Bradby Department of Electronic Materials Engineering, Research School of Physics and Engineering, Australian National University, Australia	Unexpected formation on metastable germanium polymorphs <i>J. E. Bradby, B. Haberl, J. S. Williams</i>
Inv-8 Friday 09:40-10:10 Page 19	Y. Fujiwara Graduate School of Engineering, Osaka University, Japan	Strain-dependent energy transfer from GaN host to Eu ions in Eu-doped GaN <i>Y. Fujiwara, R. Wakamatsu, A. Koizumi</i>
O-12 Friday 10:10-10:30 Page 20	M. Pravica High Pressure Science and Engineering Center (HiPSEC) and Department of Physics and Astronomy, University of Nevada, USA	Studies of gallium nitride at high pressure <i>M. Pravica, Y. Wang, D. Sneed, Q. Smith, Y. Xiao</i>
O-13 Friday 10:30-10:50 Page 21	K. Takarabe Okayama University of Science, Japan	High pressure synthesis of a few nitrides <i>K. A. Takarabe</i>
Friday 10:50-11:20	CLOSING SESSION	
Friday 11:50-17:30	CONFERENCE EXCURSION - Teotihuacan Pyramids Bus departs at 11:50 am.	

POSTER SESSION THURSDAY 7

P-01 Thursday 15:00-17:30 Page 22	Y. Kim Department of Physics, Chung-ang University, Korea	Phase-transition evidence in FeTe₂O₅Cl under pressure <i>Y. Kim, I. H. Choi, K. Y. Choi</i>
P-02 Thursday 15:00-17:30 Page 23	S. V. Ovsyannikov Bayerisches Geoinstitut, Universität Bayreuth, Germany	Semiconductor-metal transition in a ferroelectric at high pressure <i>N. V. Morozova, S. V. Ovsyannikov, Y. Vysochanskii, V. V. Shchennikov</i>
P-03 Thursday 15:00-17:30 Page 24	A. R. Goñi Institut de Ciència de Materials de Barcelona- CSIC and ICREA, Spain	High pressure study of the role planarity and intermolecular distance on the optical properties of semiconducting polymers <i>M. Schmidt, S. Foster, M. I. Alonso, D. D. C. Bradley, J. Nelson, M. Campoy-Quiles, A. R. Goñi</i>
P-04 Thursday 15:00-17:30 Page 25	A. R. Goñi ICREA and Institut de Ciència de Materials de Barcelona - CSIC, Spain	The refractive indices of wurtzite ZnO, GaN and AlN under high hydrostatic pressure <i>A. R. Goñi, F. Kaess, J. S. Reparaz, M. I. Alonso, M. Garriga, G. Callsen, M. R. Wagner, A. Hoffmann, Z. Sitar</i>
P-05 Thursday 15:00-17:30 Page 26	P. Parisiades European Synchrotron Radiation Facility, France	Structural phase stability for the SmB₆ topological insulator candidate: a high pressure and low temperature synchrotron x-ray diffraction study <i>P. Parisiades, P. Parisiades, M. Bremholm, D. Ceresoli, M. Mezouar</i>
P-06 Thursday 15:00-17:30 Page 27	J. G. Rojas-Briseño Facultad de Ciencias, Universidad Autónoma del Estado de Morelos, Mexico	Nonlinear optical properties in GaN/AlGaIn single heterostructures under hydrostatic pressure <i>J. G. Rojas-Briseño, M. E. Mora-Ramos, J. C. Martínez-Orozco</i>
P-07 Thursday 15:00-17:30 Page 28	C. A. Duque Instituto de Física, FCEN, Universidad de Antioquia, Colombia	Donor impurity-related nonlinear optical response in GaN cylindrical quantum wires: Effects of external electric field and hydrostatic pressure <i>J. D. Correa, M. E. Mora-Ramos, C. A. Duque</i>
P-08 Thursday 15:00-17:30 Page 29	K. A. Rodríguez-Magdaleno Facultad de Ciencias, Universidad Autónoma del Estado de Morelos, Mexico	High pressure effects into the absorption coefficient and relative refractive index change in an asymmetric double δ-doped GaAs quantum well <i>K. A. Rodríguez-Magdaleno, C. A. Duque, J. C. Martínez-Orozco</i>
P-09 Thursday 15:00-17:30 Page 30	C. A. Duque Instituto de Física, FCEN, Universidad de Antioquia, Colombia	Simultaneous effects of hydrostatic pressure and electric field on the electronic states and linear and nonlinear intersubband optical absorption coefficients <i>M. E. Mora-Ramos, C. A. Duque, D. A. Ospina</i>
P-10 Thursday 15:00-17:30 Page 31	C. A. Duque Instituto de Física, FCEN, Universidad de Antioquia, Colombia	Exciton-related optical properties in zincblende GaN/InGaIn quantum wells under hydrostatic pressure <i>C. M. Duque, M. E. Mora-Ramos, C. A. Duque</i>
P-11 Thursday 15:00-17:30 Page 32	S. S. Santos Instituto de Física, Universidad de Sao Paulo, Brazil	Physical properties of hydrogen in MgO: pressure effects <i>S. S. Santos, R. Larico, L. V. C. Assali, J. F. Fusto</i>

P-12 Thursday 15:00-17:30 Page 33	N. Nissim Soreq NRC, Israel	Optical properties of the polyimide "Kapton HN" at high pressures as an indication for a phase transition <i>N. Nissim, M. Werdiger, S. Eliezer</i>
P-13 Thursday 15:00-17:30 Page 34	J. H. Marín Universidad Nacional de Colombia, Colombia	Combined effects of hydrostatic pressure, temperature and concentration in vertically stacked GaAs/Al_xGa_{1-x}As quantum magnetic-rings <i>M. R. Fulla, J. H. Marín, W. Gutiérrez</i>
P-14 Thursday 15:00-17:30 Page 35	J. H. Marín Universidad Nacional de Colombia, Colombia	Hydrostatic pressure and temperature effects on the ground state coupled donors in GaAs-Ga_{1-x}Al_xAs quantum well <i>J. H. Marín, M. R. Fulla, Y. A. Suaza</i>
P-15 Thursday 15:00-17:30 Page 36	A. Jiménez-González Instituto de Energías Renovables - UNAM, Mexico	Energy band gap behavior in nanostructured TiO₂ system as a pressure function in the hydrothermal treatment and their application in dye sensitized solar cells (DSSC) <i>M. A. Sánchez-García, X. Bokhimi, A. E. Jiménez-González</i>
P-16 Thursday 15:00-17:30 Page 37	J. Rivera Departamento de Ciencias Básicas, Universidad Autónoma Metropolitana-Azcapotzalco, Mexico	Effects of spin-orbit coupling on actinium under pressure <i>A. Rubio-Ponce, J. Rivera, D. Olguín</i>
P-17 Thursday 15:00-17:30 Page 38	E. Martínez-Piñero IIM, UNAM, Mexico	Electronic properties in a single crystal of FeSe_{0.5}Te_{0.5} under high pressure <i>E. Martínez-Piñero, R. López-Romero, R. Escudero</i>
P-18 Thursday 15:00-17:30 Page 39	S. S. Santos Instituto de Física, Universidade de Sao Paulo, Brazil	Effects of aluminum in MgSiO₃ in the earth's lower mantle <i>R. Larico, S. S. Santos, M. L. M. Santos, L. V. C. Assali, J. F. Justo</i>
P-19 Thursday 15:00-17:30 Page 40	E. V. Mejía-Uriarte Centro de Ciencias Aplicadas y Desarrollo Tecnológico - UNAM, Mexico	Coordination change in KBr: Eu²⁺ single crystal induced by high pressure <i>E. V. Mejía-Uriarte, F. Rodríguez, J. A. Barreda, O. Kolokoltsev, E. Camarillo, J. Hernández-A., H. Murrieta-S.</i>
P-20 Thursday 15:00-17:30 Page 41	V. V. Kolomoets Institute of Semiconductor Physics, National Academy of Sciences of Ukraine, Ukraine	Low-temperature plasticity in high uniaxially strained Ge and Si. Interface model of phenomenon <i>V. V. Kolomoets, V. M. Ermakov, V. F. Machulin, L. I. Panasjuk, E.F. Venger, E. Liarokapis, L. Taimuratova, B. Orasgulyjev</i>
P-21 Thursday 15:00-17:30 Page 42	R. Debord ILM-CNRS, France	Localization of propagative phonons in a perfectly crystalline solid <i>S. Pailhes, H. Euchner, V. M. Giordano, R. Debord, A. Assy, S. Gomes, A. Bosak, D. Machon, S. Paschen, M. de Boissieu</i>